

Title (en)

EPOXY RESIN COMPOSITION AND SEMICONDUCTOR SEALING MATERIAL COMPRISING SAME

Publication

**EP 0379172 A3 19920226 (EN)**

Application

**EP 90100919 A 19900117**

Priority

- JP 768489 A 19890118
- JP 768589 A 19890118
- JP 869289 A 19890119

Abstract (en)

[origin: EP0379172A2] Disclosed is an epoxy resin composition comprising, as basic components, (A) an epoxy resin, (B) a phenol-novolak resin, (C) a curing promotor and (D) a filler. Pulverized or spherical silica having specific particle size characteristics is used as the filler (D). Preferably, a halogenated epoxy resin and antimony oxide are further incorporated in this epoxy resin. This epoxy resin composition shows a very small molding shrinkage. If a dialkylurea derivative is used as the curing promotor (C), the stability of the composition at about 100 DEG C is drastically improved and the flowability of the composition is improved. Accordingly, precision injection molding becomes possible, and the effect of sealing a semiconductor is enhanced.

IPC 1-7

**C08L 63/04; C08G 59/44; C08K 3/34; C08K 3/20; H01L 23/29; C08G 59/40**

IPC 8 full level

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**C08L 63/00** (2006.01); **H01B 3/40** (2006.01); **H01L 23/29** (2006.01); **H01L 23/31** (2006.01)

CPC (source: EP KR US)

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Citation (search report)

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- [A] EP 0293977 A2 19881207 - SHELL INT RESEARCH [NL]
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US10079188B2; WO2017174384A1; WO0234832A1; US7527250B2; EP2826801B1

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DOCDB simple family (application)

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